

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	1398	etch with SiN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:40
S3	2	S2 with selectiv\$\$ with Aluminum adj Oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:49
S4	33	S2 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:49
S5	0	S4 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:49
S6	942	HF adj10 solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:50
S7	19	S6 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:04
S8	0	S7 with SiN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:51
S9	3	S7 with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:53
S10	579	HF with organic with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:05
S11	9	S10 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 15:54

S12	217	Etch\$4 with (Si OR silicon) adj nitride with (Al OR aluminum) adj ox\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 15:57
S13	116	S12 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:06
S14	1	S13 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 15:57
S15	15	S13 and solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 15:58
S16	1	S14 and HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 15:58
S17	21	S13 and HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 15:59
S18	1	S13 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:06
S19	0	S13 with alcohol	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:06
S20	2726	(HF OR flori\$4) with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:07
S21	47	S20 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:08

S22	4	S21 with (Al or Aluminun)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:08
S23	1883	selectivity with Aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:21
S24	253	S23 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:09
S25	0	S24 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:09
S26	114	ALON and HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:51
S27	11	S26 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:56
S28	719	Hf with etch with nitride ajd on adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:57
S29	0	Hf with etch with nitride adj on adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:57
S30	356	Hf with etch with nitride with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:58
S31	1	S30 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 16:58

S32	28	S30 with select\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 17:02
S33	61	hf with organic with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:06
S34	135233	wet adj etch nitride with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:07
S35	3943	S34 with (HF OR flori\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:07
S36	797	wet adj etch with nitride with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:08
S37	196	S35 and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:46
S38	5220	select\$4 with nitride with (AL OR AL2O3 OR aluminum adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:54
S39	560	S38 with (HF OR flour\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:51
S40	543	S38 with (HF OR flor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:49
S41	1	S40 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:48

S42	0	S40 with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:48
S43	3	S39 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:52
S44	18	S39 with organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:53
S45	6739	etch\$4 with nitride\$4 with oxide\$4 with selectiv\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:03
S46	904	S45 and organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:57
S47	296	S46 and (flour\$4 or HF)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:57
S48	296	S47 and oxide\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 07:58
S49	11571	selectiv\$4 with (AlO OR aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:09
S50	275	S49 with (SiO2 or (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:06
S51	6	S50 with (HF or flour\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:06

S52	905	selectiv\$4 with (aluminum adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:09
S53	5	S52 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:16
S64	6810	etch with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:20
S69	12966	selectivity with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:21
S70	2799	S69 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:22
S71	1333	S70 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:22
S72	38	S71 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:25
S73	0	S72 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:24
S74	0	S72 with alchohol	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:25
S75	2167	HF with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:42

S76	45	S75 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:25
S77	4	S76 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:25
S78	211	HF with EG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:28
S79	28	S78 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:29
S80	5	S79 with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:29
S81	5	S80 with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:31
S82	285	trench with etch with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:32
S83	2	S81 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:32
S84	2	S81 with nitrid\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:32
S85	132	via with etch with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:32

S86	3	S85 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:34
S87	80	nitrid\$4 with oxid\$4 with selectiv\$4 with HF with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:00
S88	1	S87 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:35
S89	0	S87 with organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:35
S90	1	S87 with organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:42
S91	0	S87 with EG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:35
S92	905	selectiv\$4 with aluminum adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:43
S93	5	S92 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:48
S94	2213	HF and 49%	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:48
S95	19696	HF and 50%	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:49

S96	2450	HF and 50% adj wt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 08:50
S97	7	HF adj 50% adj wt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:08
S98	807	etch with nitride with aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:08
S99	11	S98 with hf	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:35
S10 0	188984	aluminum with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:19
S10 1	58936	Al2O3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:19
S10 2	3021	Al2O3 with Aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:19
S10 3	9	S102 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:24
S10 4	15	"309940"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:23
S10 5	12342	etch with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:35

S10 6	323	S105 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:36
S10 7	5	S106 with aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 09:36
S10 8	42	silicon with nitrid\$4 with selectiv\$4 with oxide with HF with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:02
S10 9	632	etch with nitride with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:04
S11 0	11	S109 with aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:03
S11 1	3893640	etch adj\$5 nitride with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:05
S11 2	13405	S111 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:05
S11 3	465	S112 with aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:06
S11 4	6810	etch with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:06
S11 5	43	S114 with nitride adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:11

S11 6	2	"4269654".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:17
S11 7	226	metal adj oxid\$4 with make with transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:21
S11 8	16416	metal adj oxid\$4 with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:20
S11 9	89	metal adj oxid\$4 with make with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:23
S12 0	195	metal adj oxid\$4 adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:28
S12 1	32	metal adj oxid\$4 with coat with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:32
S12 2	3231822	metal adj oxid\$4 with coat with n or p	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:29
S12 3	1917	metal adj oxid\$4 with coat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:29
S12 4	0	S123 with N+	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:29
S12 5	10909	silicon adj oxide with aluminum adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:32

S12 6	53	S125 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:51
S12 7	4800	dielectric adj oxides	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:51
S12 8	4920	dielectric adj oxid\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:52
S12 9	53	S128 with aluminum adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:51
S13 0	109	double adj dielectric with layer\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 11:00
S13 1	4	S130 with aluminum adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:53
S13 2	2	S130 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 10:59
S13 3	9	S130 with aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 11:02
S13 4	10	S130 with (aluminum OR "Al.sub. 2O.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 11:02
S13 6	2	"4269654".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 11:21

S13 7	2	"6617190".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 15:41
S14 1	1	"20050061768"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 13:37
S14 6	19	Fluorinated adj surfactants aqueous adj acid adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 11:27
S14 7	1414	1% with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:21
S14 8	52	S147 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 13:38
S14 9	93	"L2" with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 13:38
S15 0	1	S148 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:04
S15 1	4	S147 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:04
S15 2	2167	solvent with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:14
S15 3	49	S152 with clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:15

S15 4	0	S153 with 1%	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:15
S15 5	0	S153 with 5%	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:16
S15 6	0	S153 with 10%	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:16
S15 7	0	S153 with 15%	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:16
S15 8	2559	10% with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:21
S15 9	441	10% adj HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:21
S16 0	1	S159 with solvent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:21
S16 6	0	"60606604"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 07:49
S16 7	8	"6087273"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 07:51
S16 8	9	"5885903"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 07:51

S16 9	5978	silicon adj nitride with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:38
S17 0	866	(silicon adj nitride) same (isolation adj trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:38
S17 1	607	S170 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:38
S17 2	838	S170 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:38
S17 3	591	S171 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:39
S17 4	0	S173 and almin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:39
S17 5	0	S173 and Al2O3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:39
S17 6	470	S173 and Al	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:40
S17 7	2264593	S176 and Al adj\$3 oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:40
S17 8	470	S176 and (Al adj\$3 oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:42

S17 9	26	(nitride adj selectiv\$4 same metal) with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:01
S18 0	0	(nitride adj selectiv\$4) with alimin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:02
S18 1	390	(nitride adj selectiv\$4) with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:51
S18 2	26	S181 with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:19
S18 3	1397	trench with metal adj oxid\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:06
S18 4	2	S182 with metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:03
S18 5	30531	trench with ((metal adj oxid\$3) not adj\$3 semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:07
S18 6	27	S183 not semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:17
S18 7	12	S182 not plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:20
S18 8	3	S187 not slurry	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:23

S18 9	10246	etch with nitride with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:23
S19 0	358	S189 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:23
S19 1	5	S190 with alumin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:48
S19 2	3254	wet adj etch with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:50
S19 3	547	S192 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:50
S19 4	0	S193 with over adj Almin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:49
S19 5	0	S193 with (almin\$4 adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:49
S19 6	0	S193 and (almin\$4 adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:50
S19 7	1867	wet adj etch with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:50
S19 8	815	wet adj etch with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:50

S19 9	73	S198 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:51
S20 0	0	S199 with alumin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 13:51
S20 1	15	S199 not plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:08
S20 2	529	hf with carboxylic adj acid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:09
S20 3	1	S202 with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:10
S20 4	2	S202 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:11
S20 5	360	etch same nitride.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:12
S20 6	19	S205 and HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:38
S20 7	1	double adj dielectric with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:38
S20 8	226	double adj dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:39

S209	19	S208 and HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:38
S210	80588	silicon with (oxide and alumin\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:40
S211	6443	S210 and HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:40
S212	2923	S211 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:41
S213	0	S212 and aluminun adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:41
S214	1936	S212 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:41
S215	1391	S214 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:42
S216	856	S215 and wet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:42
S217	0	(silicon adj oxide) with (aluminun adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:43
S218	3329	(silicon adj oxide) with (alumina)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:43

S21 9	4594	(silicon adj oxide) same (alumina)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:43
S22 0	115	(silicon adj oxide) same (alumina). ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:43
S22 1	2	S220 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:44
S22 2	16118	barrier adj materials	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:44
S22 3	391	barrier adj material\$3 with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:44
S22 4	5	S223 with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:47
S22 5	187	trench and nitride adj selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:47
S22 6	34	S225 and hF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 16:15
S22 7	5	etch with alumina with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:53
S22 8	604	alumina with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:53

S229	48	S228 with stop adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 16:09
S230	0	S229 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 14:54
S231	13	(nitride adj selectiv\$3) with alumin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 16:16
S232	0	("2004/0147054").URPN.	USPAT	OR	ON	2005/05/18 16:18
S233	5362632	nitride adj\$3 over adj\$3 alumin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:53
S234	14429	nitride with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:54
S235	9663	S234 with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:54
S236	788	S235 with aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:54
S237	457	S236 with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:54
S238	12	S237 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:58
S239	1391	S234 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:59

S240	33	S239 with HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:59
S241	0	S240 with alumin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 07:59
S244	3423838	(etch\$4 remove\$4 roughen\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:00
S245	365684	((aluminum Al) adj oxide) AlOx "AlO.sub.x" "AlO.subx" AlOn "AlO. subn" "AlO.sub.n" alumina)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:01
S246	210701	(SiN (Silicon adj nitride) SiNx SixNx Si3N4 "Si.sub3.Nsub.4" "Si.sub3.N. sub.x" "Si.subx.N.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:01
S247	181485	(HF (hydrogen adj fluoride) hydrofluoric (fluoric adj acid))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:02
S248	18	S244 with S245 with S246 with S247	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:02
S249	18211	S244 with S245	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:03
S250	417	S249 with S246	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:03
S251	18	S250 with S247	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:03

S25 2	17	S251 with (solvent glycol glycerol carboxylic acid polyol ethanol alcohol)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:05
S25 3	0	S251 same (solvent glycol glycerol carboxylic acid polyol ethanol alcohol).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 11:05
S25 4	20	(surface with (roughening or etch or removal)) with (silver adj (ion or nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:43
S25 5	1	"4652465".PN.	USPAT; USOCR	OR	ON	2005/05/19 12:29
S25 6	1	"0595944".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 12:40
S25 7	0	09/0595944	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 12:40
S25 8	0	US20040099637	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 12:40
S25 9	0	US20040099637	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 12:40
S26 0	0	10/0099637	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 12:41
S26 1	0	10/99637	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 12:41
S26 2	2	2000US-0595944	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 13:44

S26 3	1	10/421293	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 14:00
S26 4	0	09/595944	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 14:00
S26 5	0	09/595944	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 14:01
S26 6	0	09/595944.ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 14:01
S26 7	2	"09595944"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 14:38
S26 8	745	(halide adj ion) with (silver adj ion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:43
S26 9	8	S268 with (etch\$4 remove\$4 roughen\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:45
S27 0	0	S269 with crystal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:45
S27 1	745	(halide adj ion) with (silver adj ion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:48
S27 2	251	S271 with crystal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:48

S27 3	39	roughen\$4 etch with HF with silver with halide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:56
S27 4	2117	surface with treat\$5 with (halide or (halide adj ion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:59
S27 5	985	S274 with silver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:57
S27 6	985	S275 with (silver Ag)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:58
S27 7	1029	S274 with (silver Ag)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:58
S27 8	1	S277 with azole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:58
S27 9	447724	surface with treat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:59
S28 0	487478	surface with (treat\$5 roughen44 etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 08:59
S28 1	1283605	copper Cu (copper adj clad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 09:01
S28 2	5236309	azole silver (silver adj nitride) Au	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 09:02

S28 3	597593	halide chlorine bromine flourine iodine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 09:03
S28 4	854255	ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 09:03
S28 5	41	S280 with S281 with S283 with S284	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 09:06
S28 6	5	S285 with ppm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 09:07
S28 7	13911	glycolic adj acid and ((ethylene adj glycol) or glycerol)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 09:36
S28 8	2074	glycolic adj acid same ((ethylene adj glycol) or glycerol)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 09:37
S28 9	200	(glycolic adj acid same ((ethylene adj glycol) or glycerol)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 09:37
S29 0	2	"4269654".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:01
S29 1	9	ethanol same (ethylene adj glycol) same etchant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:09
S29 2	7	"1,160,945".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:10

S29 3	3528739	GB "1,160,945"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:10
S29 4	7	("3293148" "3481877" "3810797" "4477290").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:14
S29 5	12159	(Chelat\$3 ajd agent\$3) same ethanol same alumi\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:15
S29 6	10	(Chelat\$3 ajd agent\$3) same ethanol same alumi\$3.ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:00
S29 7	10	((Chelat\$3 ajd agent\$3) same ethanol same alumi\$3).ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:17
S29 8	1098012	(Chelat\$3 ajd agent\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:17
S29 9	376996	ethanol	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:18
S30 0	909269	alumi\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:18
S30 1	12159	S298 same S299 same S300	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:18
S30 2	10	(S298 same S299 same S300).ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:07
S30 3	50	chealating	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:19
S30 4	56726	chelating	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:19
S30 5	0	(S304 same S299 same S300).ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:19
S30 6	10	(S304 same S299).ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:59
S30 7	0	great adj britain same "1160945"	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:35

S308	0	"1160945" near anderson	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:35
S309	0	"1160945" same Anderson	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:36
S310	2	"1160945" and Anderson	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:37
S311	0	"1160945" and (United adj Kingdom)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:46
S312	0	"1160945-pal.#-\$did."	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:46
S313	0	"1160945 pal.#-\$did."	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:46
S314	16980	chelate and ethanol	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:00
S315	4854	Chelat\$3 same ethanol	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:01
S316	17	(Chelat\$3 same ethanol).ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:01
S317	3045	sheetz	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:07
S318	4	sheetz same aluminum	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 14:07
S319	1694	438/745	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:03
S320	256	438/747	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:04
S321	221	438/749	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:04

S32 2	252	438/750	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:04
S32 3	360	438/757	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:04
S32 4	8	"4269654,5939336", "5976988", "3479237,6492304,4087367", 5939336,3479237,6589439"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:07
S32 5	144	"4269654", "5939336", "5976988", "3479237", "6492304", "4087367", "5939336", "3479237", "6589439"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:08
S32 6	0	"4269654.pn.", "5939336.pn.", "5976988.pn.", "3479237.pn.", "6492304.pn.", "4087367.pn.", "5939336.pn.", "3479237.pn.", "6589439.pn."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:09
S32 7	2	"4269654.pn.", "5939336.pn.", "5976988.pn.", "3479237.pn.", "6492304.pn.", "4087367.pn.", "5939336.pn.", "3479237.pn.", "6589439".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:10
S32 8	0	((("4269654.pn.") or ("5939336.pn." ") or ("5976988.pn.") or ("3479237. pn.") or ("6492304.pn.") or ("4087367.pn.") or ("939336.pn.") or ("3479237.pn.") or ("6589439. pn.")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/15 17:04
S32 9	0	((("4269654.pn.") or ("5939336.pn." ") or ("5976988.pn.") or ("3479237. pn.") or ("6492304.pn.") or ("4087367.pn.") or ("939336.pn.") or ("3479237.pn.") or ("6589439. pn.")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 15:11
S33 0	2	"4269654".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:12
S33 1	2	"5965465".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:17

S33 2	0	("5939336.pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 15:18
S33 3	0	("5976988.pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 15:18
S33 4	0	("3479237.pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 15:18
S33 5	0	("6492304.pn.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 15:19
S33 6	0	"6,492304".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:19
S33 7	0	"6,492,304".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:19
S33 8	0	"6492304".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:19
S33 9	0	"6492304".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:19
S34 0	2	"6589439".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:21
S34 1	2	"5939336".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:28

S34 2	0	"6492304".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:20
S34 3	3	"5976988".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:25
S34 4	3	"3479237".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:24
S34 5	2	"4087367".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:22
S34 6	3	"3479237".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:22
S34 7	2	"6589439".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 15:28
S34 8	2	"4959103".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 16:12
S35 1	1	"10/725434"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:39
S35 2	764199	nickel or Ni	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:49
S35 3	67735	salicide or silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:50

S35 5	1198278	align\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:50
S35 6	18632	S353 and S355	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:50
S35 7	4258	S352 and S356	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:50
S35 8	546880	semiconductor near device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:51
S35 9	2685	S357 and S358	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:51
S36 0	2933122	anneal or heat	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:52
S36 1	489615	deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:52
S36 3	377	alkaline near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:53
S36 4	1996	S359 and S360	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:53
S36 5	1607	S364 and S361	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:53

S36 7	429034	alkaline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:53
S36 8	141	S365 and S367	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:54
S36 9	141	S368 and insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:54
S37 0	141	S368 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:56
S37 1	141	S370 and S352	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:56
S37 2	410276	nickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:56
S37 3	127	S371 and S372	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:08
S37 4	8	S373 and (second near S360)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 10:58
S37 5	2330	nickel near deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:08
S37 6	2194	nickel near silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:08

S37 7	81	S375 and S376	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:20
S37 8	74	S377 and second	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:21
S37 9	0	S377 and secon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:21
S38 0	2	S378 and (second near anneal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:23
S38 1	30	(mono and di) adj silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:37
S38 2	67735	salicide or silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:38
S38 3	81	S377	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:41
S38 5	164	unreacted adj nickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:41
S38 6	98	S385 and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:41
S38 7	3	S386 and mono and di	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:50

S38 8	50	nickel and silicide and two near (heat or anneal or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:58
S38 9	48	S388 and lower	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:58
S39 0	26	S388 and (lower near temp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/08 11:58
S39 1	1279	arsenic adj implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:15
S39 2	2037	cm-3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:15
S39 3	7	S391 and S392	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:17
S39 5	4801	"1.times.10.sup.20" "cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:18
S39 6	109	S395 and S391	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:18
S39 7	4801	"1.times.10.sup.20" "cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:20
S39 8	109	S397 and S391	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:27

S399	105	S398 and source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:27
S400	105	S398 and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:27
S401	105	S399 and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:27
S402	84	S401 and poly	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:29
S403	10	S402 and nickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:31
S404	0	"1.times.10.sup.20" adj "cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:29
S405	0	S402 and nickel near (electrode or wire)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:32
S406	7930	nickel near (electrode or wire)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:32
S407	651	(anneal or bake or heat) near nickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:35
S408	2115	Nickel adj silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:35

S409	15	S407 and S408	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:49
S410	0	S409 and dinickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:35
S411	15	S409 and ((second or two) near anneal or heat or silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:50
S412	2	S409 and ((second or two) near (anneal or heat or silicide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:54
S413	73	(clean near nickel silicide) and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:55
S414	0	(clean near nickel silicide) near EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:54
S415	0	(clean near arsenic) and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:55
S416	0	(clean near arsenic) and choline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:55
S417	0	(arsenic adj clean) and choline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:56
S418	0	(arsenic adj clean) and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:56

S41 9	0	(implant adj clean) and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:56
S42 0	59	(clean near wafer) and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:59
S42 1	0	(clean near wafer) near EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:56
S42 2	12	H2O2 and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 14:59
S42 3	3	S422 and nickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 15:01
S42 4	31	implant adj residue	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 15:03
S42 5	8	S424 and peroxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 15:09
S42 6	67	nickel near anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:56
S42 7	0	nickel near two-step adj anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 15:13
S42 8	81	two-step adj anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 15:13

S429	66448	silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/11 15:14
S430	47	S428 and S429	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:53
S431	2	"6,207,563".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:51
S432	0	("1.times.10.sup.20") adj ("cm.sup.-3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:39
S433	0	"1.times.10.sup.20" and "cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:40
S434	4810	"1.times.10.sup.20"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:40
S435	65600	arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:40
S436	19	S434 near S435	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:40
S437	2	"6767614".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:44
S438	0	("6767614").URPN.	USPAT	OR	ON	2005/07/12 12:46
S439	2	"6207563".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:52

S44 0	81	two-step adj anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:53
S44 1	66495	silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:53
S44 2	47	S440 and S441	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:53
S44 3	47	S442	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:54
S44 4	0	S443 and US6767614	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:53
S44 5	20	S443 and nickel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:54
S44 6	67	nickel near anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:56
S44 7	22	S446 and step	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 12:56
S44 8	24	("5198390" "5199917" "5235187" "5287082" "5316979" "5363021" "5375033" "5393375" "5399415" "5436070" "5449903" "5498312" "5501893" "5506175" "5546988" "5563343" "5610335" "5627427" "5628917" "5637539" "5640133" "5846849" "5847454" "5856722").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 12:58
S44 9	0	("6767614").URPN.	USPAT	OR	ON	2005/07/12 12:59

S45 0	0	US04/30289	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/12 17:00
S45 1	2	"6589829"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:10
S45 2	2	"6797614"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 14:17
S45 3	2	09/859142	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 07:41
S45 4	1	10/725434	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 11:27
S45 5	2	"6352872".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 11:29
S46 6	4	"6599370"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:52
S46 7	284254	insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:10
S46 8	72370	(plug or contact) near metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:11
S46 9	5061867	temperature or degree	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:11

S47 0	0	S468 near S467 near S469	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:11
S47 1	75	S468 near S467	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:12
S47 2	0	S471 near S469	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:12
S47 3	490508	deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:12
S47 4	43	S471 and S473	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:12
S47 5	28	S474 and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:53
S47 6	0	surface near arsenic near removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:54
S47 7	0	implant near residue near removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:54
S47 8	65660	arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:54
S47 9	138993	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:55

S48 0	588841	residue	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:55
S48 1	1941	S478 near S479	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:55
S48 2	1941	S481 and S478	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:55
S48 3	883	S481 near S478	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:55
S48 4	883	S483 and arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:55
S48 5	1	S484 and ((remove or etch) near (residue or compound))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:57
S48 6	1	S484 and ((remove or etch) near (residue or compound or contamination))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:57
S48 7	305292	contamination	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 16:57
S48 8	57	S484 and S487	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:00
S48 9	1673428	remove	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:00

S49 0	138993	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:00
S49 1	181649	contaminants	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:00
S49 2	464570	contaminat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:00
S49 3	2	S489 near S490 near S492	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:02
S49 4	692	S489 near S490	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:02
S49 5	0	S489 near S490 near compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:02
S49 6	0	S489 near S490 near residue	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:02
S49 7	3	S489 near S490 near residual	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:03
S49 8	29455	choline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:05
S50 0	26403	NH3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:05

S50 1	429561	alkaline	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:05
S50 2	65660	arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:05
S50 3	1	S498 and S499 and S500 and S501 and implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:06
S50 4	3	S498 and S500 and S501 and implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:06
S50 5	121	S498 and S500 and S501	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:06
S50 6	6	S498 and S499 and S500 and S501	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:07
S50 7	675	EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:07
S50 8	611354	ammonia or (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH. subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:09
S51 0	245396	peroxide or (Hydrogen adj peroxide) or (H2O2 or "H.sub.2O. sub.2" or "H.sub.xO.sub.x" or "H. sub.nO.sub.n" or "H.sub.xO.sub.n" or "H.sub.nO.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:10
S51 1	76	S507 and S508 and S509	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:11

S51 2	1	S511 and arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 17:11
S51 3	0	asenic adj clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:14
S51 4	0	asenic near clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 08:14
S51 5	247345	doped or dopant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:41
S51 6	2148946	clean or remove or etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:41
S51 7	882	S515 near S516	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:41
S51 8	218	S515 adj S516	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:42
S51 9	62	S518 and arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:43
S52 0	0	arsenic near S518	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:42
S52 1	0	S519 and EKC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:43

S52 2	0	S519 and peroxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/18 11:43
S52 3	17	09/770997	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 19:07
S52 4	2	09/959759	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 19:07
S52 5	873336	nickel or Ni	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:41
S52 6	1628620	silicide or si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:41
S52 7	5304	S525 adj S526	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:41
S52 8	12433778	form\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:42
S52 9	755	S527 near S528	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:43
S53 0	211	S529 and anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:43
S53 1	303058	anneal or (heat adj treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:43

S53 2	402	S529 and S531	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:43
S53 3	204	S532 and "400"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:44
S53 5	76	S533 and (S525).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 14:47
S53 6	11	S535 and monosilicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 07:55
S53 7	636743	ammonia or (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH. subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 07:57
S53 8	256895	peroxide or (Hydrogen adj peroxide) or (H2O2 or "H.sub.2O. sub.2" or "H.sub.xO.sub.x" or "H. sub.nO.sub.n" or "H.sub.xO.sub.n" or "H.sub.nO.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 07:57
S53 9	5009	S537 near S538	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:05
S54 1	3345	arsenic near impurity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:07
S54 2	5324571	element region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:06
S54 3	1271	isolation near insulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:06

S54 4	25134	diffusion near region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:06
S54 5	172737	gate near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:07
S54 6	519955	mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:07
S54 7	33	concentration near cm-3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:09
S54 8	559	S541 and S544	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:07
S54 9	13	S541 and S543	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:08
S55 0	1885	S541 and S545	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:08
S55 1	1616	S550 and S546	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:08
S55 3	1336162	concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:08
S55 4	2003	arsenic near implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:11

S55 6	768	S545 and S554	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:10
S55 7	413192	isolation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:10
S55 8	447	S556 and S557	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:10
S55 9	447	S545 and S558	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:10
S56 0	2142	cm-3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:11
S56 2	69334	arsenic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:11
S56 4	150	S560 and S562	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:12
S56 5	0	S559 and S564	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:12
S56 6	81	S564 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:13
S56 7	16	S566 and (ni or nickel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:13

S56 8	10	S567 and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:31
S56 9	2	"6589829".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 08:31